## Amendment to the Claims:

- 1. (Original) A method of creating a design for a semiconductor memory, comprising:
  - a. providing a leaf cell design for use by a memory compiler for a semiconductor memory, the leaf cell design further comprising a power management circuit design as a leaf cell for a memory circuit;
  - b. acquiring a user input describing a parameter of a circuit, the circuit to comprise the leaf cell design;
  - c. providing a user-selectable option to selectively allow enablement of an ultra low power feature; and
  - d. creating a semiconductor memory design by the memory compiler which incorporates the power management circuit in a compiled semiconductor memory macro when the user-selectable option is enabled.
- 2. (Original) The method of claim 1, wherein the memory compiler is adapted to create a design for at least one of (1) a static random access memory, (ii) a read only memory, (iii) an embedded flash memory, or (iv) a single transistor random access memory.
- 3. (Original) The method of claim 1, wherein the power management circuit design is adapted to reduce leakage power resulting from a circuit resulting from use of the memory compiler.
- 4. (Original) The method of claim 1, wherein the power management circuit design is adapted to provide a first control voltage power supply adapted to provide power to a circuit peripheral to a memory cell array and to provide a second control voltage power supply adapted to provide power to the memory cell array.

U.S. Patent Application Serial No.: 10/752,116

Art Unit No.: 2825

5. (Original) The method of claim 4, wherein the power management circuit design comprises:

- a. a first control supply voltage design, adapted to produce the first control voltage power supply; and
- b. a second control supply voltage design, adapted to produce the second control voltage power supply;
- c. wherein the second control voltage power supply is a separate voltage supply with respect to the first control voltage power supply.
- 6. (Currently Amended) A method of creating a design for a semiconductor memory, comprising:
  - a. providing a leaf cell design for use by a memory compiler for a semiconductor memory, the leaf cell design further comprising a power management circuit design as a leaf cell for a memory circuit;
  - b. acquiring a user input describing a parameter of a circuit, the circuit to comprise the leaf cell design;
  - c. providing a user-selectable option to selectively allow enablement of an ultra low power feature; and
  - d. creating a semiconductor memory design by the memory compiler which incorporates the power management circuit in a compiled semiconductor memory macro when the user-selectable option is enabled

wherein the power management circuit design is adapted to provide a first control voltage power supply adapted to provide power to a circuit peripheral to a memory cell

U.S. Patent Application Serial No.: 10/752,116

Art Unit No.: 2825

array and to provide a second control voltage power supply adapted to provide power to the memory cell array

e. The method of claim 5, further comprising-providing the control supply voltage of the memory periphery circuit with a netlist identifier which is unique with respect to a netlist identifier for the control supply voltage of the memory cell

wherein the power management circuit design comprises:

- (i) a first control supply voltage design, adapted to produce the first control voltage power supply; and
- (ii) a second control supply voltage design, adapted to produce the second control voltage power supply;
- (iii) wherein the second control voltage power supply is a separate voltage supply with respect to the first control voltage power supply.
- 7. (Original) The method of claim 5, wherein the first control voltage power supply further comprises:
  - a. a voltage supply; and
  - b. a control signal.
- 8. (Original) The method of claim 7, wherein the voltage supply is a variable voltage supply which may be used to provide a substantially zero voltage.
- 9. (Original) The method of claim 5, wherein the second control voltage supply is a variable voltage supply, further comprising:

U.S. Patent Application Serial No.: 10/752,116

Art Unit No.: 2825

a. allowing the second control voltage supply to operate in a minimum voltage level capable of sustaining data in the memory cell; and

- b. allowing the second control voltage supply to have a substantially zero voltage in a static mode.
- 10. (Original) A graphical user interface, displayable on a computer display, configured to allow a user to specify a parameter for a power management circuit design as a leaf cell for a memory circuit, comprising a region of a visually perceptible display accessible by a user of a computer system, the region further comprising a user selectable option to specify selection or deselection of an ultra low power feature of power management circuit design as a leaf cell.
  - 11. (Original) An electronic circuit created using the process of claim 1.